

Features

- Ultra-Low Input Bias Current:
 - ± 1 pA (Max) at $T_A = 25^\circ\text{C}$ (Lab Test Limit)
 - ± 30 pA (Max) at $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ (Lab Test Limit)
- Low Input Offset Voltage: ± 250 μV (Max)
- Integrated Guard Buffer with 200- μV Maximum Offset
- Low Voltage Noise Density: 18 nV/ $\sqrt{\text{Hz}}$ at 1 kHz
- Wide Bandwidth: 2.1 MHz
- Supply Voltage: 4.5 V to 16 V (± 2.25 V to ± 8 V)
- Rail-to-Rail Output Swing
- ESD Rating: Robust 3-kV HBM, 1.5-kV CDM

Applications

- Photodiode Sensor Interface
- Industrial Sensors and Instrumentation
- A.T.E. Leakage Testing

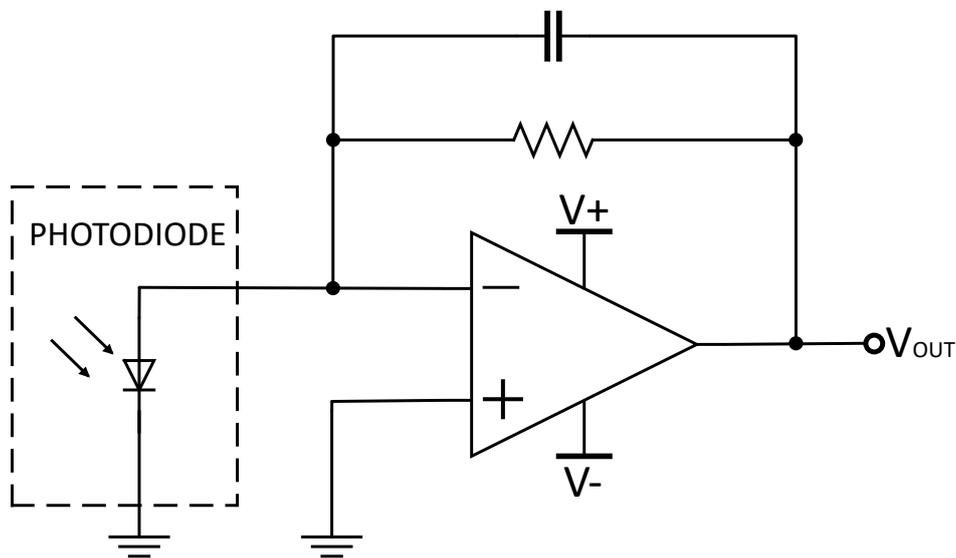
Description

The TPA3531 and TPA3532 operational amplifiers feature very low input bias current. They operate from 4.5 V to 16 V (± 2.25 V to ± 8 V), and feature rail-to-rail output swing in addition to an input common-mode range that includes ground. The integrated guard buffer isolates the input pins from leakage in the printed circuit board. They minimize board component counts and enable easy system design.

The TPA3531 and TPA3532 are ideal for portable medical and industrial applications that require low-bias current analog front-end performance, such as photodiode trans-impedance and chemical sensor interface circuits.

The TPA3531 and TPA3532 are available in the SOT23-5, MSOP8, and SOP8 packages, and are specified over the industrial temperature range from -40°C to $+125^\circ\text{C}$.

Typical Application Circuit



Trans-Impedance Amplifier with Photodiode

Table of Contents

Features	1
Applications	1
Description	1
Typical Application Circuit	1
Revision History	3
Pin Configuration and Functions	4
Specifications	6
Absolute Maximum Ratings ⁽¹⁾	6
ESD, Electrostatic Discharge Protection.....	6
Recommended Operating Conditions.....	6
Thermal Information.....	6
Electrical Characteristics.....	8
Electrical Characteristics (Continued).....	10
Detailed Description	12
Overview.....	12
Feature Description.....	12
Application and Implementation	13
Application Information	13
Typical Application.....	13
Layout	15
Layout Guideline.....	15
Tape and Reel Information	16
Package Outline Dimensions	17
SOP8.....	17
MSOP8.....	18
SOT23-5.....	19
Order Information	20
IMPORTANT NOTICE AND DISCLAIMER	21

Revision History

Date	Revision	Notes
2025-03-20	Rev.A.0	Initial version.

Pin Configuration and Functions

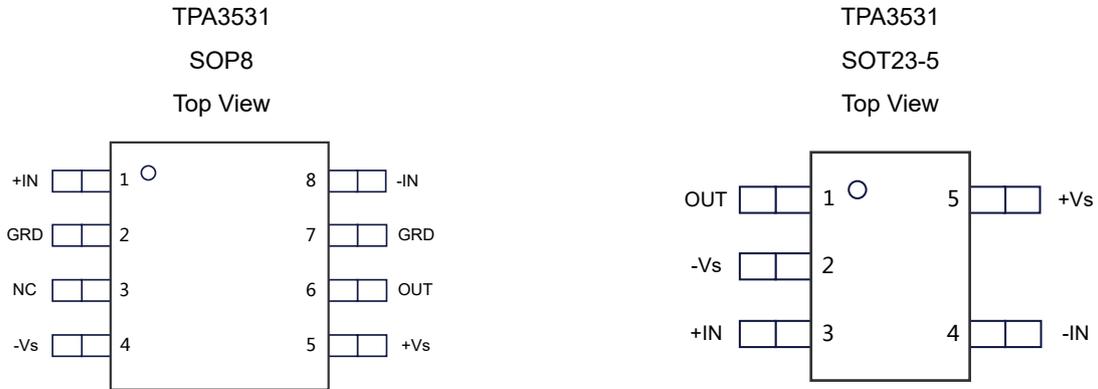
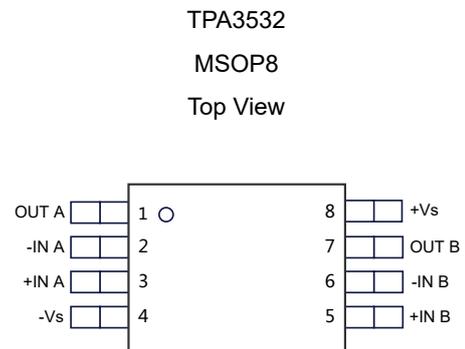
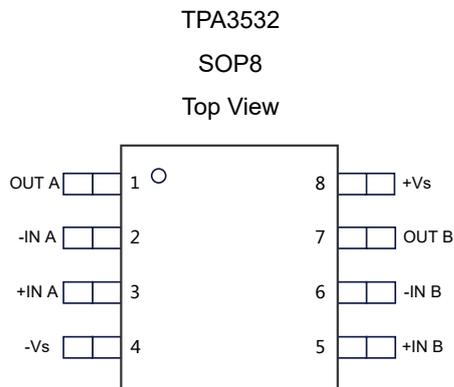


Table 1. Pin Functions: TPA3531

Pin No.		Name	I/O	Description
SOP8	SOT23-5			
1	3	+IN	I	Non-inverting input.
2		GRD	O	Guard.
3		NC	–	No internal connection.
4	2	-Vs	–	Negative power supply.
5	5	+Vs	–	Positive power supply.
6	1	OUT	O	Output.
7		GRD	O	Guard.
8	4	-IN	I	Inverting input.


Table 2. Pin Functions: TPA3532

Pin No.	Name	I/O	Description
1	OUT A	O	Output
2	-IN A	I	Inverting input
3	+IN A	I	Non-Inverting input
4	-Vs		Negative power supply
5	+IN B	I	Non-Inverting input
6	-IN B	I	Inverting input
7	OUT B	O	Output
8	+Vs		Postive power supply

Specifications

Absolute Maximum Ratings ⁽¹⁾

Parameter		Min	Max	Unit
Supply Voltage	$(+V_S) - (-V_S)$		17	V
Signal Input Pins ⁽²⁾	Voltage	$(-V_S) - 0.3$	$(+V_S) + 0.3$	V
	Current	-10	10	mA
Differential Input Voltage	Differential ($V_{+IN} - V_{-IN}$)	-7	7	V
Output Short Current	Short Circuit to Ground	Indefinite		
T_A	Operating Temperature Range	-40	125	°C
T_J	Junction Temperature Range		150	°C
T_{stg}	Storage Temperature Range	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

(2) The input pins are diode-clamped to the power-supply rails. The input signal current that can swing more than 0.3 V beyond the supply rails must be limited to 10 mA or less.

ESD, Electrostatic Discharge Protection

Symbol	Parameter	Condition	Minimum Level	Unit
HBM	Human Body Model ESD	ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	3	kV
CDM	Charged Device Model ESD	ANSI/ESDA/JEDEC JS-002 ⁽²⁾	1.5	kV

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Recommended Operating Conditions

Parameter		Min	Typ	Max	Unit
V_S	Supply Voltage	4.5 (± 2.25)		16 (± 8)	V
V_{IN}	Signal Input Pins	$-V_S$		$(+V_S) - 1.5$	V
T_A	Operating Ambient Temperature	-40		125	°C

Thermal Information

Package Type	θ_{JA}	θ_{JC}	Unit
SOP8	158	43	°C/W
SOT23-5	158	71	°C/W

Ultra Low Input Bias Current Amplifier

Package Type	θ_{JA}	θ_{JC}	Unit
MSOP8	120	41	°C/W

Electrical Characteristics

All test conditions: $V_S = (+V_S) - (-V_S) = 4.5\text{ V}$, $T = 25^\circ\text{C}$, $V_{CM} = V_S / 2$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$, unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Power Supply						
I_Q	Quiescent Current per Amplifier	$I_{OUT} = 0\text{ mA}$		0.9	1.4	mA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1.5	
PSRR	Power Supply Rejection Ratio	$V_S = 4.5\text{ V to }16\text{ V}$	115	127		dB
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	110			
Input Characteristics						
$I_B^{(1)}$	Input Bias Current		-1	0.2	1	pA
		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$	-10		10	
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$, RH < 50%	-30		30	
$I_{OS}^{(1)}$	Input Offset Current	RH < 50%	-0.5	± 0.1	0.5	pA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$, RH < 50%	-15		15	
V_{OS}	Input Offset Voltage	$V_{CM} = 0\text{ V to }1.5\text{ V}$	-250		250	μV
		$V_{CM} = 1.5\text{ V to }3\text{ V}$	-300		300	
		$V_{CM} = 0\text{ V to }3\text{ V}$, $-40^\circ\text{C} < T_A < 125^\circ\text{C}$	-750		750	
$V_{OS\text{ TC}}$	Input Offset Voltage Drift	$-40^\circ\text{C} < T_A < 125^\circ\text{C}$		2		$\mu\text{V}/^\circ\text{C}$
V_{CM}	Input Common-Mode Voltage		0		3	V
CMRR	Common-Mode Rejection Ratio	$V_{CM} = 1.5\text{ V to }3\text{ V}$	86			dB
		$V_{CM} = 1.5\text{ V to }3\text{ V}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	84			
		$V_{CM} = 0\text{ V to }3\text{ V}$	75			
A_{OL}	Open-Loop Gain	$R_L = 2\text{ k}\Omega\text{ to }V_{CM}$, $V_{OUT} = 0.2\text{ V to }4.3\text{ V}$	122			dB
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	120			
R_{IN}	Input Resistance	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		>100		T Ω
C_{IN}	Input Capacitance			10		pF
Output Characteristics						
V_{OH}	Output Voltage High	$R_L = 10\text{ k}\Omega\text{ to }V_{CM}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	4.46			V
		$R_L = 2\text{ k}\Omega\text{ to }V_{CM}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	4.38			
V_{OL}	Output Voltage Low	$R_L = 10\text{ k}\Omega\text{ to }V_{CM}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			40	mV

Ultra Low Input Bias Current Amplifier

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$R_L = 2\text{ k}\Omega$ to V_{CM} , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			120	
I_{SC}	Short-Circuit Current	Source current		31		mA
		Sink current		19		
AC Electrical Characteristics						
GBW	Gain Bandwidth			2.1		MHz
SR	Slew Rate			1.4		V/ μ s
V_N	Input Voltage-Noise Density	$f = 1\text{ kHz}$		18		nV/ $\sqrt{\text{Hz}}$
V_{NP-P}	Input Voltage Noise	$f = 0.1\text{ Hz to }10\text{ Hz}$		4		μ V _{P-P}
C_{LOAD}	Capacitive Loading	No sustained oscillations		100		pF
Guard Buffer						
V_{GOS}	Guard Offset Voltage	$V_{SUPPLY} = 5\text{ V}$, $V_{CM} = V_{SUPPLY} / 2$	-200		200	μ V

(1) Guaranteed by design. +IN and -IN are internally connected to the gates of the CMOS transistors. CMOS GATE leakage is so small that it is impractical to test in production. Devices are screened during production testing to eliminate defective units.

Electrical Characteristics (Continued)

All test conditions: $V_S = (+V_S) - (-V_S) = 16\text{ V}$, $T = 25^\circ\text{C}$, $V_{CM} = V_S / 2$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$, unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Power Supply						
I_Q	Quiescent Current per Amplifier	$I_{OUT} = 0\text{ mA}$		0.9	1.4	mA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1.5	
PSRR	Power Supply Rejection Ratio	$V_S = 4.5\text{ V to }16\text{ V}$	115	127		dB
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	110			
Input Characteristics						
$I_B^{(1)}$	Input Bias Current	$RH < 50\%$	-1	± 0.2	1	pA
		$-40^\circ\text{C} < T_A < +80^\circ\text{C}$, $RH < 50\%$	-10		10	
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$, $RH < 50\%$	-30		30	
$I_{OS}^{(1)}$	Input Offset Current	$RH < 50\%$	-0.5	± 0.1	0.5	pA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$, $RH < 50\%$	-15		15	
V_{OS}	Input Offset Voltage	$V_{CM} = 0\text{ V to }1.5\text{ V}$	-250		250	μV
		$V_{CM} = 1.5\text{ V to }14.5\text{ V}$	-300		300	
		$V_{CM} = 0\text{ V to }14.5\text{ V}$, $-40^\circ\text{C} < T_A < 125^\circ\text{C}$	-750		750	
$V_{OS\text{ TC}}$	Input Offset Voltage Drift	$-40^\circ\text{C} < T_A < 125^\circ\text{C}$		2		$\mu\text{V}/^\circ\text{C}$
V_{CM}	Input Common-Mode Voltage		0		14.5	V
CMRR	Common-Mode Rejection Ratio	$V_{CM} = 1.5\text{ V to }14.5\text{ V}$	104			dB
		$V_{CM} = 1.5\text{ V to }14.5\text{ V}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	102			
		$V_{CM} = 0\text{ V to }14.5\text{ V}$	95			
A_{OL}	Open-Loop Gain	$R_L = 2\text{ k}\Omega\text{ to }V_{CM}$, $V_{OUT} = 0.5\text{ V to }15.5\text{ V}$	127			dB
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	125			
R_{IN}	Input Resistance	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		>100		T Ω
C_{IN}	Input Capacitance			10		pF
Output Characteristics						
V_{OH}	Output Voltage High	$R_L = 10\text{ k}\Omega\text{ to }V_{CM}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	15.9			V
		$R_L = 2\text{ k}\Omega\text{ to }V_{CM}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	15.58			
V_{OL}	Output Voltage Low	$R_L = 10\text{ k}\Omega\text{ to }V_{CM}$, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			100	mV

Ultra Low Input Bias Current Amplifier

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$R_L = 2\text{ k}\Omega$ to V_{CM} , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			420	
I_{SC}	Short-Circuit Current	Source current		33		mA
		Sink current		21		
AC Electrical Characteristics						
GBW	Gain Bandwidth			2.1		MHz
SR	Slew Rate			1.4		V/ μ s
V_N	Input Voltage-Noise Density	$f = 1\text{ kHz}$		18		nV/ $\sqrt{\text{Hz}}$
V_{NP-P}	Input Voltage Noise	$f = 0.1\text{ Hz to }10\text{ Hz}$		4		μ V _{P-P}
C_{LOAD}	Capacitive Loading	No sustained oscillations		100		pF
Guard Buffer						
V_{GOS}	Guard Offset Voltage	$V_{SUPPLY} = 5\text{ V}$, $V_{CM} = V_{SUPPLY} / 2$	-200		200	μ V

(1) Guaranteed by design. +IN and -IN are internally connected to the gates of the CMOS transistors. CMOS GATE leakage is so small that it is impractical to test in production. Devices are screened during production testing to eliminate defective units.

Detailed Description

Overview

The TPA3531/TPA3532 can interface with small signals from either current sources or high-output impedance voltage sources. Applications include photodiode pulse oximeters, pH sensors, capacitive pressure sensors, chemical analysis equipment, smoke detectors, and humidity sensors. The TPA3531/TPA3532 features a combination of low-input current, rail-to-rail output voltage swing, wide-supply voltage range, and low-power operation.

Feature Description

Input Bias and Guard Buffer

The TPA3531/TPA3532 features a MOS-input stage with only 1pA (max) of input bias current. The unique input diode structure provides ESD protection, and allows the diodes to be guarded to minimize leakage currents at the input pins. The TPA3531/TPA3532 integrates a precision buffer that guards internal ESD diode leakage paths. The buffer input is connected to the non-inverting input (+IN) which is approximately equal to the input common-mode voltage when the main amplifier feedback loop is settled.

The output of this guard buffer is also connected to external pins (GRD), allowing users to guard external components against leakage currents. The input bias current is determined by the accuracy of the guard voltage applied across the ESD diodes.

Input Common-Mode Voltage

The TPA3531/TPA3532 is a rail-to-rail output amplifier with an input voltage range from $(-V_S)$ to $(+V_S) - 1.5$ V. The input guard buffer supports rail-to-rail output that allows the guard voltage to swing within 100 mV of the supply rails. Because the guard buffer output follows the input common-mode voltage, this output range limits the effectiveness of the guard buffer at low-input common-mode voltages. For this reason, it is not recommended to operate the circuit with an input common-mode voltage of less than 100 mV from the $-V_S$ supply rail.

Rail-to-Rail Output Stage

The TPA3531/TPA3532 output stage swings to within 30 mV (typ) of either power-supply rail with a 100-k Ω load, and provides a 2.1-MHz GBW with a 1.4-V/ μ s slew rate. The device is also unity-gain stable.

Application and Implementation

Note

Information in the following application sections is not part of the 3PEAK's component specification and 3PEAK does not warrant its accuracy or completeness. 3PEAK's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

Application Information

The TPA3531/TPA3532 is a single CMOS operational amplifier with very low input bias current and offset voltage. It is suited for a wide variety of current output transducers (such as photodiodes and photomultiplier tubes), spectrometry, chromatography, and high-impedance buffering for chemical sensors.

Power Supply

The TPA3531/TPA3532 operates from +4.5 V to +16 V (± 2.25 V to ± 8 V). Bypass the power-supply inputs, $+V_S$ and $-V_S$, to a quiet copper ground plane, with a 0.1- μ F IC capacitor in parallel with a 4.7- μ F electrolytic capacitor, placed close to the pins.

High-Impedance Sensor Front Ends

The TPA3531/TPA3532 interfaces include photodiodes and potentiated sensors, and high-impedance voltage sources, such as pH sensors. It is designed to maximize the performance of high-impedance circuits.

Typical Application

Figure 1 shows the TPA3531/TPA3532 configured in a trans-impedance amplifier interfacing with a photodiode.

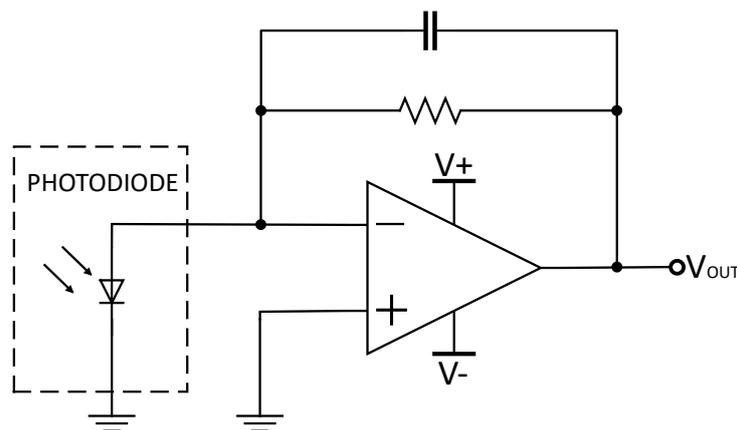


Figure 1. Trans-Impedance Amplifier with Photodiode

TIA Application Recommendations

It is essential to take into account various noise sources. Op amp noise voltage, feedback resistor thermal noise, input noise current, and photodiode noise current do not operate across the same frequency range when analyzing the noise at the output of the TIA. The op amp noise voltage is gained up within the range between the noise gain zero and its pole. The higher the values of R_F and C_{IN} are (C_{IN} is the total capacitance at the inverting terminal of the op amp, including the photodiode capacitance and input capacitance), the sooner the noise gain peaking starts, and the larger its contribution to

the total output noise is. An equivalent total-noise voltage is calculated by taking the square root of the sum of squared contributing noise voltages at the output of TIA.

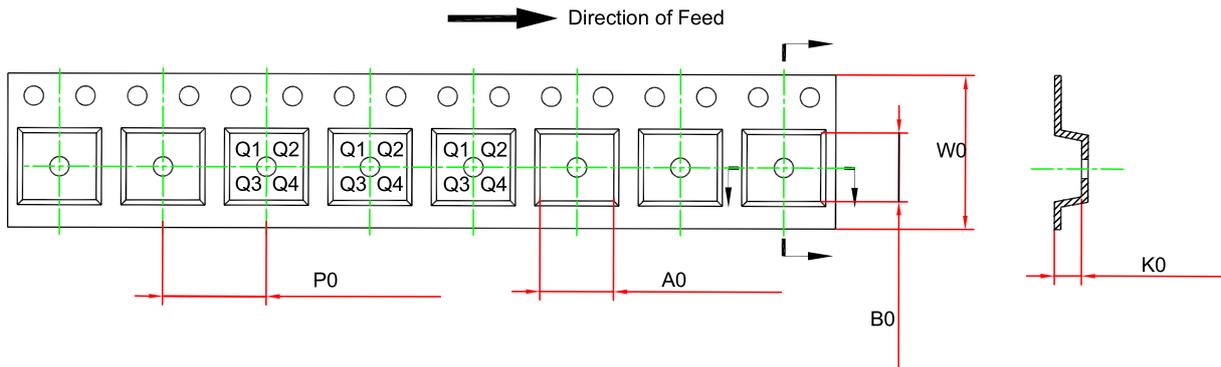
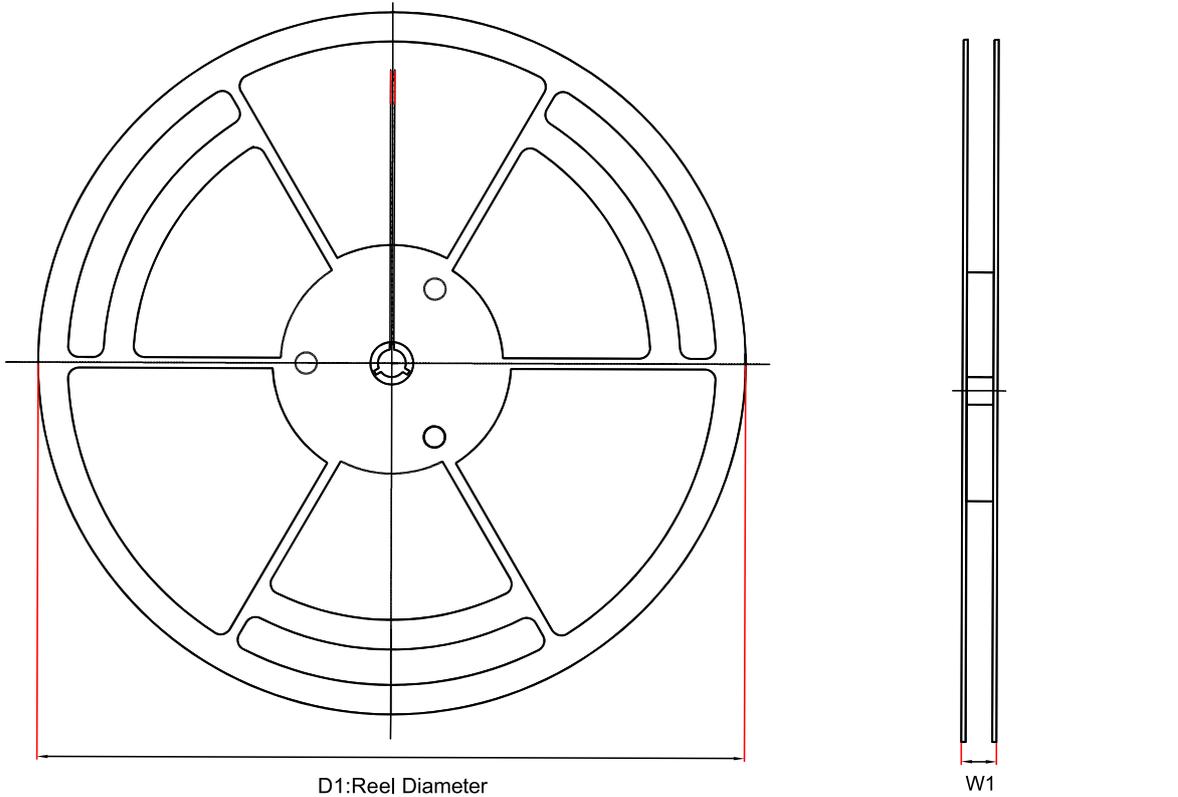
Layout

Layout Guideline

A good layout is critical to obtaining high performance, especially when interfacing with high-impedance sensors. Use shielding techniques to guard against parasitic leakage paths. The goal of guarding is to completely surround the insulation of the high-impedance node with another conductor that is driven to the guard voltage. The guard rail isolates sensitive nodes, such as the inverting input and the traces connecting to it, from varying or large-voltage differentials that otherwise occur in the rest of the circuit board. This reduces leakage and noise effects, allowing accurate sensitive measurements.

Be careful when decreasing the amount of stray capacitance at the inputs of op amp to improve stability. To achieve this, minimize trace lengths and resistor leads by placing external components as close as possible to the package. If the sensor is inherently capacitive or is connected to the amplifier through a long cable, use a low-value feedback capacitor to control high-frequency gain and peaking to stabilize the feedback loop.

Tape and Reel Information

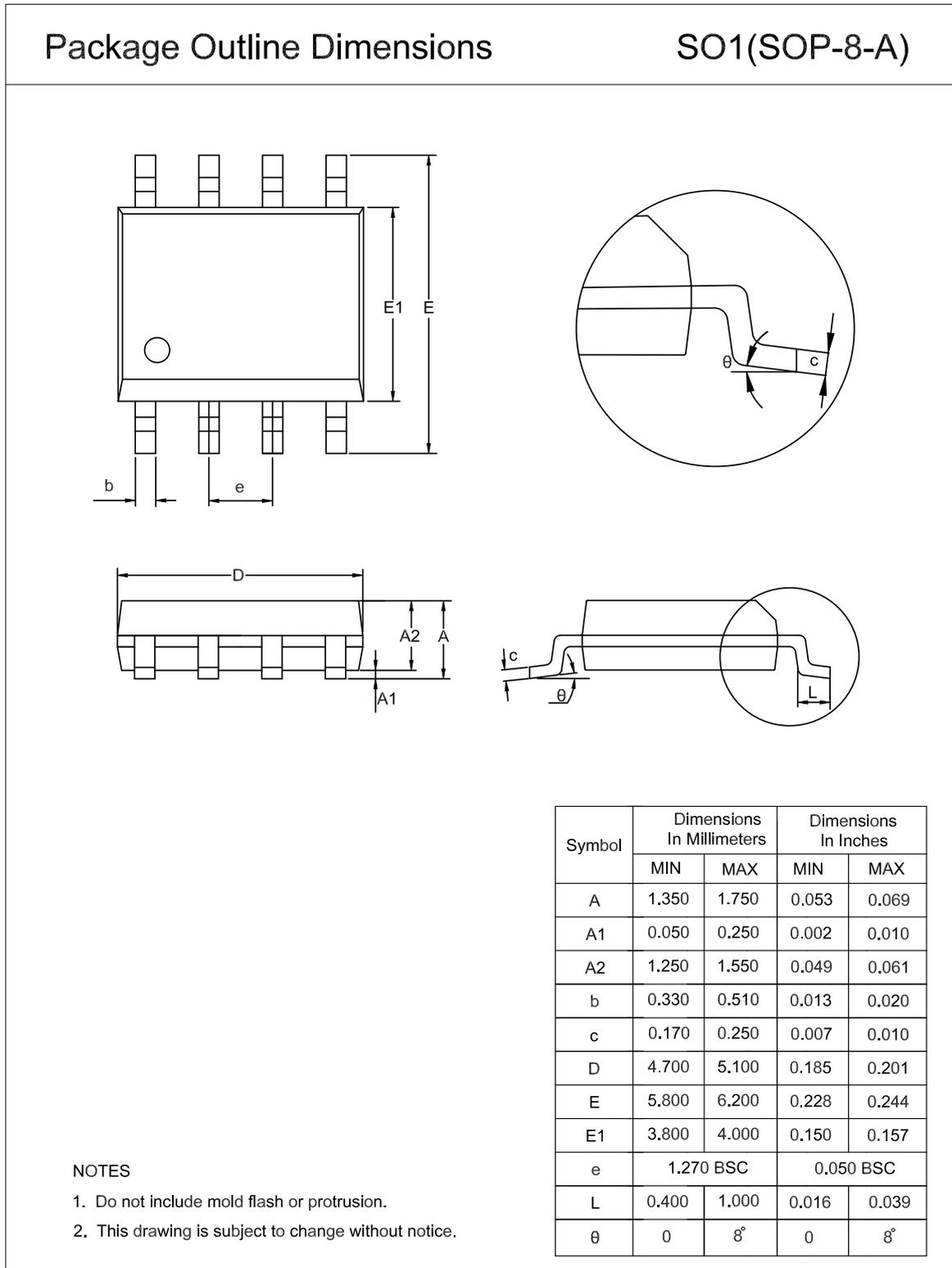


Order Number	Package	D1 (mm)	W1 (mm)	A0 (mm) ⁽¹⁾	B0 (mm) ⁽¹⁾	K0 (mm) ⁽¹⁾	P0 (mm)	W0 (mm)	Pin1 Quadrant
TPA3531-SO1R	SOP8	330	17.6	6.5	5.4	2	8	12	Q1
TPA3531-S5TR	SOT23-5	179	12	3.3	3.25	1.4	4	8	Q3
TPA3532-SO1R	SOP8	330	17.6	6.5	5.4	2	8	12	Q1
TPA3532-VS1R	SOP8	330	17.6	5.3	3.4	1.3	8	12	Q1

(1) The value is for reference only. Contact the 3PEAK factory for more information.

Package Outline Dimensions

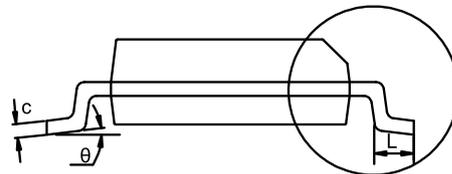
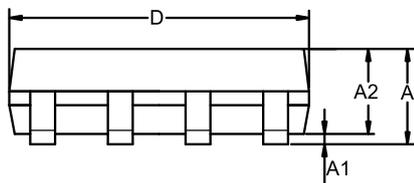
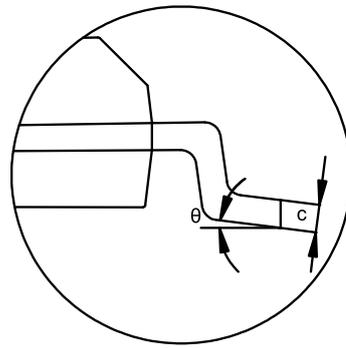
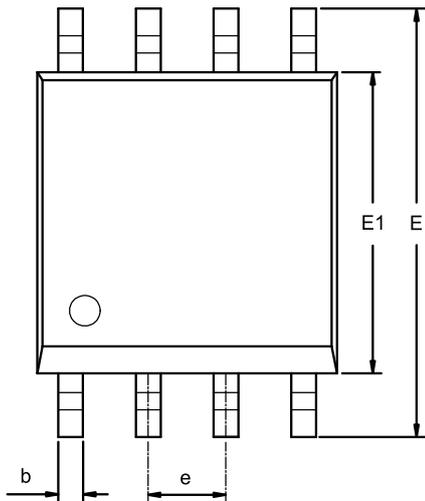
SOP8



MSOP8

Package Outline Dimensions

VS1(MSOP-8-A)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.800	1.100	0.031	0.043
A1	0.020	0.150	0.001	0.006
A2	0.750	0.950	0.030	0.037
b	0.250	0.380	0.010	0.015
c	0.090	0.230	0.004	0.009
D	2.900	3.100	0.114	0.122
E	4.700	5.100	0.185	0.201
E1	2.900	3.100	0.114	0.122
e	0.650 BSC		0.026 BSC	
L	0.400	0.800	0.016	0.031
θ	0	8°	0	8°

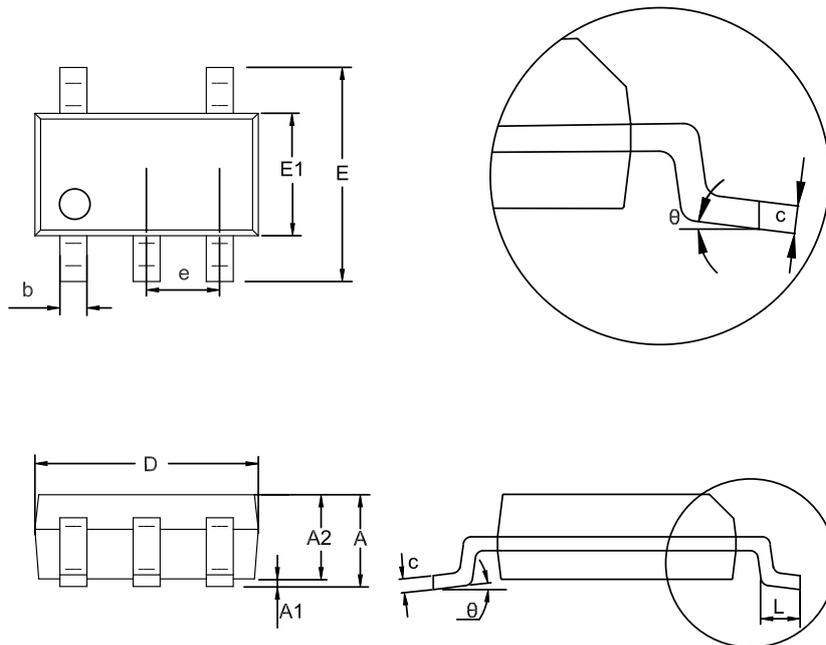
NOTES

1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.

SOT23-5

Package Outline Dimensions

S5T(SOT23-5-A)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	1.050	1.250	0.041	0.049
A1	0.000	0.150	0.000	0.006
A2	1.000	1.200	0.039	0.047
b	0.280	0.500	0.011	0.020
c	0.100	0.230	0.004	0.009
D	2.820	3.020	0.111	0.119
E	2.600	3.000	0.102	0.118
E1	1.500	1.720	0.059	0.068
e	0.950 BSC		0.037 BSC	
L	0.300	0.600	0.012	0.024
theta	0	8°	0	8°

NOTES

1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.

Order Information

Order Number	Operating Temperature Range	Package	Marking Information	MSL	Transport Media, Quantity	Eco Plan
TPA3531-SO1R	-40 to 125°C	SOP8	A3531	2	Tape and Reel, 4000	Green
TPA3531-S5TR	-40 to 125°C	SOT23-5	A9S	3	Tape and Reel, 3000	Green
TPA3532-SO1R	-40 to 125°C	SOP8	A3532	3	Tape and Reel, 4000	Green
TPA3532-VS1R	-40 to 125°C	MSOP8	A3532	3	Tape and Reel, 3000	Green

Green: 3PEAK defines "Green" to mean RoHS compatible and free of halogen substances.

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